IN THE SPECIFICATION

Please insert the following paragraph after Title:

CROSS-REFERENCE TO RELATED APPLICATION

This application is a Continuation of co-pending U.S. Patent Application Serial No. 09/592,587, filed June 12, 2000, and claims priority to Japanese Patent Applications No. 11-167872, filed June 15, 1999, and No. 11-266956, filed September 21, 1999. The contents of these applications are incorporated herein by reference in their entirety.

Please amend the paragraph on page 10, lines 6-7, as follows:

Figure 3 is a cross sectional view showing a transfer electrode of embodiment 3 of the present invention; [[and]]

Please amend the paragraph on page 10, lines 8-9, as follows:

Fig. 4 is a cross sectional view showing a conventional transfer electrode;

Fig. 5 is a cross sectional view showing a transfer electrode and the second metal film;

Fig. 6 is a cross sectional view showing a transfer electrode and the first metal film; and

Fig. 7 is a cross sectional view showing a transfer electrode, first and second metal films, a thin film transistor, and a pixel electrode.

Please amend the paragraph beginning on page 10, line 14, to page 11, line 10, as follows:

Referring to Fig. 1, the following description will discuss the EMBODIMENT 1 of the present invention. Fig. 1 shows a cross-cross cross sectional view of a transfer electrode in the EMBODIMENT 1 of the present invention, and the following description will discuss the construction together with the functions thereof. Here, the construction in which an electrical potential is connected to the common electrodes (conductive thin film) on the opposing substrate side from the transfer electrode on the array substrate through the conductive material is the same as that shown in Fig. 4~~; therefore, the description thereof is omitted~~. Fig. 1 shows a cross-sectional shape of the transfer electrode on an array substrate side of a liquid crystal display constituted by a pair of insulating substrates that are joined to each other with a liquid crystal layer interpolated in between; and reference number 1 is an insulating substrate (array substrate), 2 is a transfer electrode, 3 is a metal film of the second layer from the substrate face and that has been formed in the second conductive film forming process of the insulating substrate 1, 4 is an insulating film of the second layer formed after the metal film 3 as the second layer, 5 is an insulating film of the first layer formed after the metal film as the first layer formed in the first conductive film forming process of the insulating substrate 1, 6 is a transparent conductive thin film that is formed in the last conductive film forming process of the insulating substrate 1 and that forms the transfer electrode 2, and 7 is a contact hole.

Please amend the paragraph beginning on page 11, lines 11-25, as follows:

When an electrical potential is supplied to the common electrodes on the opposing substrate, a conductive material is applied to the center portion of the transfer electrode 2, and this is connected to an electrode section on the opposing substrate. Fig. [1] 5 shows a case in which a common electrical potential on the insulating substrate 1 is supplied to the transfer

electrode section through the metal film 3 as the second layer that has been formed in the second conductive film forming process of the insulating substrate 1. The metal film 3 supplies the common electrical potential to the conductive thin film 6 through the contact hole 7 in the vicinity of the transfer electrode 2, and the common electrical potential is transferred to a conductive material 9 and to a common electrode 11 on the second insulating substrate 10. [[and]] In this construction, the conductive thin film 6 allows at least one portion in the center portion of the transfer electrode 2 to be directly formed on the insulating substrate 1. In the present specification, one portion refers to a range of approximately 10 % to 90 % of the opening section of the transfer electrode 2.

Please amend the paragraph beginning on page 12, line 25, to page 13, line 20, as follows:

Referring to Fig. 2, the following description will discuss the EMBODIMENT 2. Fig. 2 shows a cross-cross cross sectional view of a transfer electrode in the EMBODIMENT 2 of the present invention, and the following description will discuss the construction together with the functions thereof. Here, the construction in which an electrical potential is connected to the common electrodes (conductive thin film) on the opposing substrate side from the transfer electrode on the array substrate through the conductive material is the same as that shown in Fig. 4~~; therefore, the description thereof is omitted~~. Fig. 2 shows a cross-sectional shape of the transfer electrode on an array substrate side of a liquid crystal display constituted by a pair of insulating substrates that are joined to each other with a liquid crystal layer interpolated in between; and reference number 1 is an insulating substrate (array substrate); 2 is a transfer electrode; 4 is an insulating film of the second layer that is formed after a metal film of the second layer that has been formed in the second conductive film

forming process of the insulating substrate 1; 5 is an insulating film of the first layer that is formed after a metal film of the first layer that has been formed in the first conductive film forming process of the insulating substrate 1; 6 is a conductive thin film formed in the last conductive film forming process of the insulating substrate 1; 7 is a contact hole; and 8 is a metal film of the first layer formed in the first conductive film forming process of the insulating substrate 1.

Please amend the paragraph beginning on page 13, line 21, to page 14, line 19, as follows:

When an electrical potential is supplied to the common electrodes on the opposing substrate, a conductive material is applied to the center portion of the transfer electrode 2, and this is connected to an electrode section on the opposing substrate. Fig. [[2]] 6 shows a case in which a common electrical potential on the insulating substrate 1 is supplied to the transfer electrode section through the metal film 8 as the first layer that has been formed in the first conductive film forming process of the insulating substrate 1. The metal film 8 supplies the common electrical potential to the conductive thin film 6 through the contact hole 7 in the vicinity of the transfer electrode 2, and the common electrical potential is transferred to a conductive material 9 and to a common electrode 11 on the second insulating substrate 10. [[and]] In this construction, the conductive thin film 6 allows at least one portion in the center portion of the transfer electrode 2 to be directly formed on the insulating substrate 1. Moreover, Fig. 2 has exemplified the structure in which the metal film 8 is placed under the insulating films 4 and 5, and since no insulating film that is subjected to etching is located under the metal film 8, no problem arises as to the coverage of the conductive thin film 6 so that the metal film 8 may be removed at the same positions as

the insulating films 4 and 5. Moreover, in the case of the metal film 8 having a shape that allows it to expose toward the center portion from the insulating films 4 and 5, it is not necessary to provide a structure having individual contact holes as shown in Fig. 2, and the metal film 8 is allowed to directly contact the conductive thin film 6 by removing the insulating films 4 and 5 on the exposed portion of the metal film 8 upon removing the insulating films 4 and 5 at the center portion of the opening section of the transfer electrode 2, thereby making it possible to supply the common electrical potential.

Please amend the paragraph beginning on page 15, line 8, to page 16, line 5, as follows:

Referring to Fig. 3, the following description will discuss the EMBODIMENT 3 of the present invention. Fig. 3 shows a cross-cross cross sectional view of a transfer electrode in the EMBODIMENT 2 of the present invention, and the following description will discuss the construction together with the functions thereof. Here, the construction in which an electrical potential is connected to the common electrodes (conductive thin film) on the opposing substrate side from the transfer electrode on the array substrate through the conductive material is the same as that shown in Fig. 4~~; therefore, the description thereof is omitted~~. Fig. 3 shows a cross-sectional shape of the transfer electrode on an array substrate side of a liquid crystal display constituted by a pair of insulating substrates that are joined to each other with a liquid crystal layer interpolated in between; and reference number 1 is an insulating substrate (array substrate); 2 is a transfer electrode; 3 is a metal film of the second layer that is formed in the second conductive film forming process of the insulating substrate 1; 4 is an insulating film of the second layer that is formed after a metal film 3 that has been formed in the second conductive film forming process of the insulating substrate 1;

5 is an insulating film of the first layer that is formed after a metal film 8 of the first layer that has been formed in the first conductive film forming process of the insulating substrate 1; 6 is a conductive thin film formed in the last conductive film forming process of the insulating substrate 1; 7 is a contact hole; and 8 is a metal film of the first layer formed in the first conductive film forming process of the insulating substrate 1.

Please amend the paragraph on page 16, line 6, to page 17, line 6, as follows:

When an electrical potential is supplied to the common electrodes on the opposing substrate, a conductive material is applied to the center portion of the transfer electrode 2, and this is connected to an electrode section on the opposing substrate. Fig. [[3]] 7 shows a case in which a common electrical potential on the insulating substrate 1 is supplied to the transfer electrode section through the metal film 8 as the first layer that has been formed in the first conductive film forming process of the insulating substrate 1 and the metal film 3 as the second layer that has been formed in the second conductive film forming process of the insulating substrate 1. The metal films 3 and 8 of the first and second layers supply the common electrical potential to the conductive thin film 6 through the contact hole 7 in the vicinity of the transfer electrode 2, and the common electrical potential is transferred to a conductive material 9 and to a common electrode 11 on the second insulating substrate 10. [and] In this construction, one thin film transistor (TFT) is shown formed on the substrate 1 of the first metal film 8, the first insulating film 5, a semiconductor pattern 13 layered on the insulating film 5, an n-type semiconductor pattern 14 layered on the semiconductor pattern 13, and a second metal film 3 as a source/drain electrode pattern layer 15 formed on the n-type semiconductor pattern 14 (millions of TFT are formed on the substrate). In addition, a pixel electrode 12 if formed on the TFT, and the conductive thin film 6 allows at least one

portion in the center portion of the transfer electrode 2 to be directly formed on the insulating substrate 1. Moreover, Fig. 3 has exemplified the structure in which the metal film 8 of the first layer is placed under the insulating films 4 and 5; however, in the same manner as the EMBODIMENT 2, the metal film 8 may be removed at the same positions as the insulating films 4 and 5 on the center side of the transfer electrode. Moreover, in the case of the metal film 8 having a shape that allows it to expose toward the center portion from the insulating films 4 and 5, it is not necessary to provide a structure having independent contact holes on the metal film 8 of the first layer as shown in Fig. 3, and the metal film 8 is allowed to directly contact the conductive thin film 6 by removing the insulating films 4 and 5 on the exposed portion of the metal film 8 upon removing the insulating films 4 and 5 at the center portion of the transfer electrode 2, thereby making it possible to supply the common electrical potential.